Amplifier Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	BC182	Unit
Collector – Emitter Voltage	V_{CEO}	50	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

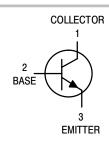
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	125	°C/W



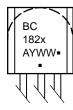
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



BC182x = Device Code x = A or B

TO-92

CASE 29

STYLE 17

A = Assembly Location

Y = Year WW = Work Week • Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC182	TO-92	5000 Units / Box
BC182G	TO-92 (Pb-Free)	5000 Units / Box
BC182A	TO-92	5000 Units / Box
BC182AG	TO-92 (Pb-Free)	5000 Units / Box
BC182B	TO-92	5000 Units / Box
BC182BG	TO-92 (Pb-Free)	5000 Units / Box
BC182BRL1	TO-92	2000 / Tape & Reel
BC182BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			-	•	•	•
Collector – Emitter Breakdown Voltage $(I_C = 2.0 \text{ mA}, I_B = 0)$		V _(BR) CEO	50	-	_	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)		V _{(BR)CBO}	60	-	-	V
Emitter – Base Breakdown Voltage ($I_E = 100 \mu A$, $I_C = 0$)		V _{(BR)EBO}	6.0	-	-	V
Collector Cutoff Current (V _{CB} = 50 V, V _{BE} = 0)		І _{СВО}	-	0.2	15	nA
Emitter–Base Leakage Current (V _{EB} = 4.0 V, I _C = 0)		I _{EBO}	-	-	15	nA
ON CHARACTERISTICS			-	•	•	•
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	BC182	h _{FE}	40	-	_	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC182A BC182B		120 120 180	-	500 220 500	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182		80		-	
Collector – Emitter On Voltage ($I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$) (Note 1)		V _{CE(sat)}		0.07 0.2	0.25 0.6	V
Base – Emitter Saturation Voltage (I _C = 100 mA, I _B = 5.0 mA) (Note 1)		V _{BE(sat)}	_	-	1.2	V
Base–Emitter On Voltage (I_C = 100 μ A, V_{CE} = 5.0 V) (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 100 mA, V_{CE} = 5.0 V) (Note 1)		V _{BE(on)}	- 0.55 -	0.5 0.62 0.83	- 0.7 -	V
DYNAMIC CHARACTERISTICS		•	-			•
Current – Gain — Bandwidth Product $(I_C = 0.5 \text{ mA}, V_{CE} = 3.0 \text{ V}, f = 100 \text{ MHz})$		f⊤	_	100	-	MHz
$(I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz})$			150	200	-	
Common Base Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{ob}	-	-	5.0	pF
Common Base Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)		C _{ib}	-	8.0	-	pF
Small–Signal Current Gain ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$)	BC182 BC182A BC182B	h _{fe}	125 125 240	- - -	500 260 500	-
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2.0 k Ω , f = 1.0 kHz)		NF	_	2.0	10	dB

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.

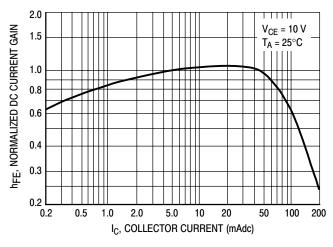


Figure 1. Normalized DC Current Gain

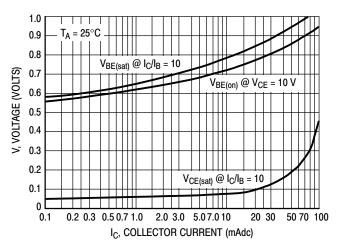


Figure 1. "Saturation" and "On" Voltages

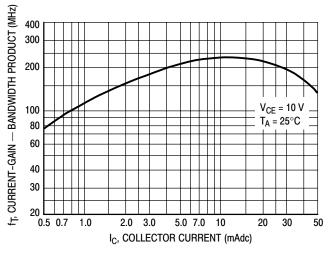


Figure 2. Current-Gain — Bandwidth Product

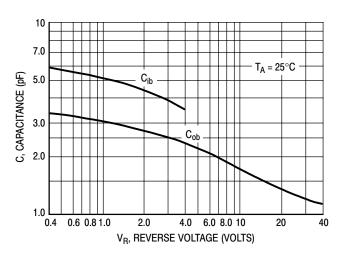


Figure 3. Capacitances

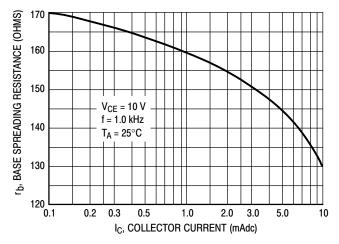
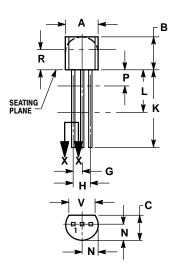


Figure 4. Base Spreading Resistance

PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11 **ISSUE AL**





- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 17:

PIN 1. COLLECTOR 2. BASE

EMITTER

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